

FORM PTO-1449  INFORMATION DISCLOSURE CITATION IN AN APPLICATION		DOCKET NUMBER SLA0871		APPLICATION NUMBER 10/825,830		
		APPLICANT Sheng Teng Hsu				
		FILING DATE: April 16, 2004		GROUP ART UNIT 2818		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE DATE IF APPROP.
TH	3,838,405	Sep., 1974	Arnett et al.	✓	✓	
	5,410,504	Apr., 1995	Ward.	365	149	
	5,508,953	Apr., 1996	Fukuda et al.	365	145	
	5,579,258	Nov., 1996	Adachi.	365	145	
	5,640,343	Jun., 1997	Gallagher et al.	365	171	
	5,712,612	Jan., 1998	Lee et al.	338	32	
	5,792,569	Aug., 1998	Sun et al.	428	692	
	5,991,193	Nov., 1999	Gallagher et al.	365	171	
	6,128,214	Oct., 2000	Kuekes et al.	365	151	
	6,198,208	Mar., 2001	Yano et al.	310	358	
	6,204,139	Mar., 2001	Liu et al.	438	385	
	6,473,332	Oct., 2002	Ignatiev et al.	365	148	
	6,479,848	Nov., 2002	Park et al.	257	295	
TH	6,569,745	May 2003	Hsu	438	385	
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO
OTHER DOCUMENTS						
TH	Wu et al., "High Temperature Retention Properties of Ferroelectric PZT/YBCO Heterostructures Investigated by Pyroelectric Current and Phase Detection," 1996, Proceedings of the Tenth IEEE International Symposium on Applications of Ferroelectrics, p. 507-510.*					
TH	Article entitled, "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", by S. Q. Liu et al., published in Applied Physics Letters, vol. 76, No. 19, May 8, 2000, pp 2749-2751.					
TH	Article entitled, "Reproducible Switching Effect in Thin Oxide Films for Memory Applications", by A. Beck et al., published in Applied Physics Letters, vol. 77, No. 1, Jul. 3, 2000, pp. 139-141.					
EXAMINER  TH STU HIO			DATE CONSIDERED  Feb. 2006			